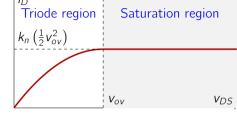


 $i_D = k_n \left( v_{ov} - \frac{1}{2} V_{DS} \right) V_{DS}$ 



Diode I-V Characteristic

MOSFET Saturation Region 
$$v_{DS} \ge v_{ov}$$

 $i_D = \frac{1}{2} k_n v_{ov}^2$